

IN THE CLAIMS

Please amend the claims as follows:

Claims 1-45 (Canceled)

46. (New) A method comprising:
forming a MEMS device on a substrate;
etching a conductive layer on the substrate to form a first ring layer and a first pad such that the MEMS device and the first pad are within the first ring layer;
forming an integrated circuit; and
bonding the first ring layer and the first pad to the integrated circuit to form a sealed cavity that includes the MEMS device and the first pad.
47. (New) The method of claim 46, wherein forming the integrated circuit includes etching a conductive layer on the integrated circuit to form a second ring layer and a second pad such that the second pad is within the second ring layer.
48. (New) The method of claim 47, wherein bonding the first ring layer and the first pad on the substrate to the integrated circuit includes bonding the first ring layer on the substrate to the second ring layer on the integrated circuit and bonding the first pad on the substrate to the second pad on the integrated circuit.
49. (New) The method of claim 46, wherein etching a conductive layer on the substrate to form a first ring layer includes etching the conductive layer to form a first rectangular ring layer on the substrate.
50. (New) The method of claim 46, wherein bonding the first ring layer and the first pad to the integrated circuit to form a sealed cavity includes bonding the first ring layer and the first pad to the integrated circuit in a controlled environment.

51. (New) The method according to claim 50, wherein bonding the first ring layer and the first pad to the integrated circuit in a controlled environment includes bonding the first ring layer and the first pad to the integrated circuit in a vacuum.

52. (New) A method comprising:
forming a MEMS device on a substrate;
etching a conductive layer on an integrated circuit to form a first ring layer and a first pad;
bonding the first ring layer and the first pad to the substrate to form a sealed cavity that includes the MEMS device and the first pad, the first pad not mechanically engaging the MEMS device.

53. (New) The method of claim 52, further comprising etching a conductive layer on the substrate to form a second ring layer and a second pad such that the MEMS device and the second pad are within the second ring layer.

54. (New) The method of claim 53, wherein bonding the first ring layer and the first pad on the integrated circuit to the substrate includes bonding the second ring layer on the substrate to the first ring layer on the integrated circuit and bonding the second pad on the substrate to the first pad on the integrated circuit.

55. (New) The method of claim 52, wherein etching a conductive layer on the integrated circuit to form a first ring layer includes etching the conductive layer to form a first rectangular ring layer on the integrated circuit.

56. (New) The method of claim 52, wherein bonding the first ring layer and the first pad to the substrate to form a sealed cavity includes bonding the first ring layer and the first pad to the substrate in a controlled environment.

57. (New) The method according to claim 56, wherein bonding the first ring layer and the first pad to the substrate in a controlled environment includes bonding the first ring layer and the first pad to the substrate in a vacuum.

58. (New) A method comprising:
forming a MEMS device on a substrate;
etching a first conductive layer on the substrate to form a first ring layer and a first pad such that the MEMS device and the first pad are within the first ring layer;
forming an integrated circuit;
etching a second conductive layer on the integrated circuit to form a second ring layer and a second pad such that the second pad is within the second ring layer;
bonding the first pad on the substrate to the second pad on the integrated circuit; and
bonding the first ring layer on the substrate to the second ring layer on the integrated circuit to form a sealed cavity that includes the MEMS device and the first and second pads.

59. (New) The method of claim 58, wherein bonding the first ring layer on the substrate to the second ring layer on the integrated circuit includes coupling the substrate to the integrated circuit in a controlled environment.

60. (New) The method according to claim 59, wherein coupling the substrate to the integrated circuit in a controlled environment includes coupling the substrate to the integrated circuit in a vacuum.

61. (New) The method of claim 58, further comprising:
etching the first conductive layer to form at least one additional pad within the first ring layer;
etching the second conductive layer to form at least one additional pad within the second ring layer; and
bonding the at least one additional pad on the substrate to the at least one additional pad on the integrated circuit within the sealed cavity.